

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,012,010 B2
APPLICATION NO. : 10/688439
DATED : March 14, 2006
INVENTOR(S) : Trung Tri Doan et al.

Page 1 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 5, line 21 –

Replace “O₃ and 88% O₂, at 4000 sccm and helium at from 014 200”
With -- O₃ and 88% O₂, at 4000 sccm and helium at from 0-200--

Col. 8, line 18, claim 5 –

Replace “powers an aspect ratio of the trench from what is was prior”
With --lowers an aspect ratio of the trench from what it was prior--

Col. 8, line, 12

Please insert the following claims:

--6. The method of claim 1 comprising solidifying material of the initially liquid deposition prior to the subsequent initially solid deposition.

7. The method of claim 1 wherein the initially liquid deposition and the initially solid deposition occur at different temperatures.

8. The method of claim 7 wherein the initially liquid deposition is conducted at temperature lower than that of the initially solid deposition.

9. The method of claim 1 comprising annealing the material of the initially liquid deposition prior to the subsequent initially solid deposition.

10. The method of claim 9 wherein the annealing is effective to solidify the material of the initially liquid deposition prior to the subsequent initially solid deposition.

11. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH₄ and H₂O₂ into a chamber within which the semiconductive substrate is received.

12. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH₄, H₂O₂, and N₂ into a chamber within which the semiconductive substrate is received.

13. The method of claim 1 wherein the initially liquid deposition comprises introducing (CH₃)_zSiH_{4-z} and H₂O₂ into a chamber within which the semiconductive substrate is received, where z is at least 1 and no greater than 4.

14. The method of claim 13 wherein the (CH₃)_zSiH_{4-z} comprises CH₃SiH₃.

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Please insert the following claims (cont'd):

- 15.** The method of claim 1 wherein material of the initially liquid deposition deposits over a base of the isolation trench faster than over sidewalls of the isolation trench.
- 16.** The method of claim 1 wherein material of the initially liquid deposition deposits over a base of the isolation trench thicker than over sidewalls of the isolation trench.
- 17.** The method of claim 1 comprising exposing material of the initially liquid deposition to ultraviolet light prior to the subsequent initially solid deposition.
- 18.** The method of claim 17 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to ultraviolet light.
- 19.** The method of claim 1 comprising exposing material of the initially liquid to an electron beam prior to the subsequent initially solid deposition.
- 20.** The method of claim 19 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to the electron beam.
- 21.** The method of claim 1 comprising exposing material of the initially liquid to a plasma prior to the subsequent initially solid deposition.
- 22.** The method of claim 21 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to plasma.
- 23.** The method of claim 1 comprising exposing material of the initially liquid deposition to RF energy prior to the subsequent initially solid deposition.

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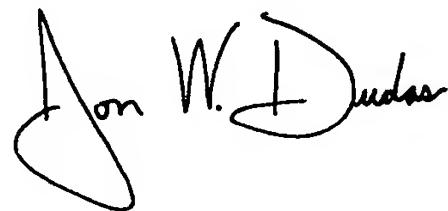
It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Please insert the following claims (cont'd):

24. The method of claim 23 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to RF energy.--

Signed and Sealed this

Seventeenth Day of July, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office